

NCS1002

Constant Voltage / Constant Current Secondary-Side Controller

Description

The NCS1002 is a highly integrated solution for Switching Mode Power Supply (SMPS) applications requiring a dual control loop to perform Constant Voltage (CV) and Constant Current (CC) regulation. The NCS1002 integrates a 2.5 V voltage reference and two precision op amps. The voltage reference, along with Op Amp 1, is the core of the voltage control-loop. Op Amp 2 is an independent, uncommitted amplifier specifically designed for the current control. Key external components needed to complete the two control loops are: (a) A resistor divider that senses the output of the power supply (battery charger) and fixes the voltage regulation set point at the specified value. (b) A sense resistor that feeds the current sensing circuit with a voltage proportional to the DC output current. This resistor determines the current regulation set point and must be adequately rated in terms of power dissipation. The NCS1002 comes in a small 8-pin SOIC package and is ideal for space-shrunk applications such as battery chargers.

Features

- Low Input Offset Voltage: 0.5 mV, Typ
- Input Common-Mode Range includes Ground
- Low Quiescent Current: 300 μ A per Op Amp at $V_{CC} = 5$ V
- Large Output Voltage Swing
- Wide Power Supply Range: 3 V to 32 V
- High ESD Protection: 2 kV
- These are Pb-Free Devices

Typical Applications

- Battery Chargers
- Switch Mode Power Supplies



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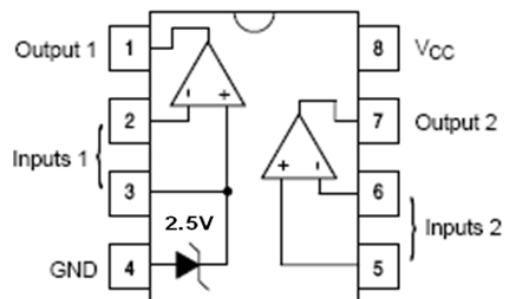
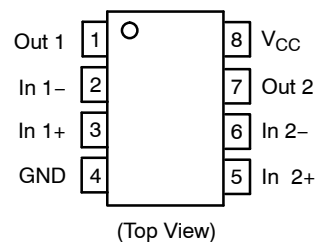
MARKING DIAGRAMS



- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

NCS1002

MAXIMUM RATINGS

Parameter	Symbol	Rating	Unit
Supply Voltage (V_{CC} to GND)	V_{CC}	36	V
Differential Input Voltage	V_{id}	36	V
Input Voltage	V_i	-0.3 to +36	V
ESD Protection Voltage at Pin Human Body Model	V_{ESD}	2000	V
Maximum Junction Temperature	T_J	150	°C
Specification Temperature Range (T_{min} to T_{max})	T_A	-40 to +105	°C
Operating Free-Air Temperature Range	T_{oper}	-55 to +125	°C
Storage Temperature Range	T_{stg}	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Parameter	Symbol	Rating	Unit
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	175	°C/W

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ELECTRICAL CHARACTERISTICS

Symbol	Characteristics	Conditions	Min	Typ	Max	Unit
I_{CC}	Total Supply Current, excluding current in the Voltage Reference $V_{CC} = 5\text{ V}$, no load; $-40 \leq T_A \leq +105^\circ\text{C}$			0.3	0.4	mA
I_{CC}	Total Supply Current, excluding Current in the Voltage Reference $V_{CC} = 30\text{ V}$, no load; $-40 \leq T_A \leq +105^\circ\text{C}$				0.75	mA

OP AMP 1 (OP AMP WITH NONINVERTING INPUT CONNECTED TO THE INTERNAL V_{ref}) ($V_{CC} = 5\text{ V}$, $T_A = 25^\circ\text{C}$ unless otherwise noted)

V_{IO}	Input Offset Voltage	$T_A = 25^\circ\text{C}$			2.0	mV
		$-40 \leq T_A \leq +105^\circ\text{C}$			3.0	mV
DV_{IO}	Input Offset Voltage Drift ($-40 \leq T_A \leq +105^\circ\text{C}$)			7.0		$\mu\text{V}/^\circ\text{C}$
I_{IB}	Input Bias Current (Inverting Input Only) $T_A = 25^\circ\text{C}$			20		nA
AVD	Large Signal Voltage Gain ($V_{CC} = 15\text{ V}$, $R_L = 2\text{ k}\Omega$, $V_{ICM} = 0\text{ V}$)			100		V/mV
PSRR	Power Supply Rejection ($V_{CC} = 5.0\text{ V}$ to 30 V , $V_{OUT} = 2\text{ V}$)		80	100		dB
I_{SOURCE}	Output Source Current ($V_{CC} = 15\text{ V}$, $V_{OUT} = 2.0\text{ V}$, $V_{id} = 1\text{ V}$)		20	40		mA
I_O	Short Circuit to GND ($V_{CC} = 15\text{ V}$)			40	60	mA
I_{SINK}	Output Current Sink ($V_{id} = -1\text{ V}$)	$V_{CC} = +15\text{ V}$, $V_{OUT} = 0.2\text{ V}$ (Note 1)	1	10		mA
		$V_{CC} = +15\text{ V}$, $V_{OUT} = 2\text{ V}$	10	20		mA
V_{OH}	Output Voltage Swing, High ($V_{CC} = 30\text{ V}$)	$R_L = 2\text{ k}\Omega$, $T_A = 25^\circ\text{C}$	26	27		V
		$-40 \leq T_A \leq +105^\circ\text{C}$	26			
		$R_L = 10\text{ k}\Omega$, $T_A = 25^\circ\text{C}$	27	28		
		$-40 \leq T_A \leq +105^\circ\text{C}$	27			
V_{OL}	Output Voltage Swing, Low	$R_L = 10\text{ k}\Omega$, $T_A = 25^\circ\text{C}$		5.0	50	mV
		$-40 \leq T_A \leq +105^\circ\text{C}$			50	
SR	Slew Rate ($AV = +1$, $V_i = 0.5\text{ V}$ to 2 V , $V_{CC} = 15\text{ V}$, $R_L = 2\text{ k}\Omega$, $C_L = 100\text{ pF}$)		0.2	0.4		V/ μs
GBP	Gain Bandwidth Product ($V_{CC} = 30\text{ V}$, $AV = +1$, (Note 1) $R_L = 2\text{ k}\Omega$, $C_L = 100\text{ pF}$, $f = 100\text{ kHz}$, $V_{IN} = 10\text{ mV}_{PP}$)		0.5	0.9		MHz
THD	Total Harmonic Distortion ($f = 1\text{ kHz}$, $AV = 10$, $R_L = 2\text{ k}\Omega$, $V_{CC} = 30\text{ V}$, $V_{OUT} = 2\text{ V}_{PP}$)			0.08		%

OP AMP 2 (INDEPENDENT OP AMP) ($V_{CC} = 5.0\text{ V}$, $T_A = 25^\circ\text{C}$ unless otherwise noted)

V_{IO}	Input Offset Voltage	$T_A = 25^\circ\text{C}$		0.5	2.0	mV
		$-40 \leq T_A \leq +105^\circ\text{C}$			3.0	
DV_{IO}	Input Offset Voltage Drift ($-40 \leq T_A \leq +105^\circ\text{C}$)			7.0		$\mu\text{V}/^\circ\text{C}$
I_{IO}	Input Offset Current	$T_A = 25^\circ\text{C}$		2.0	75	nA
		$-40 \leq T_A \leq +105^\circ\text{C}$			150	
I_B	Input Bias Current	$T_A = 25^\circ\text{C}$		20	150	nA
		$-40 \leq T_A \leq +105^\circ\text{C}$			200	
AVD	Large Signal Voltage Gain ($V_{CC} = 15\text{ V}$, $R_L = 2\text{ k}\Omega$, $V_{OUT} = 1.4\text{ V}$ to 11.4 V)	$T_A = 25^\circ\text{C}$	50	100		V/mV
		$-40 \leq T_A \leq +105^\circ\text{C}$	25			
PSRR	Power Supply Rejection ($V_{CC} = 5\text{ V}$ to 30 V)		65	100		dB

1. Guaranteed by design and/or characterization.

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ELECTRICAL CHARACTERISTICS (continued)

Symbol	Characteristics	Conditions	Min	Typ	Max	Unit
OP AMP 2 (INDEPENDENT OP AMP) (continued) ($V_{CC} = 5.0\text{ V}$, $T_A = 25^\circ\text{C}$ unless otherwise noted)						
V_{ICM}	Input Common Mode Voltage Range (Note 2) ($V_{CC} = +30\text{ V}$)	$T_A = 25^\circ\text{C}$	0		$V_{CC} - 1.5$	V
		$-40 \leq T_A \leq +105^\circ\text{C}$	0		$V_{CC} - 2.0$	
CMRR	Common Mode Rejection Ratio (Note 4)	0 to $V_{CC} - 1.7\text{ V}$, $T_A = 25^\circ\text{C}$	70	85		dB
		0 to $V_{CC} - 2.2\text{ V}$ $-40 \leq T_A \leq +105^\circ\text{C}$	60			
I_{SOURCE}	Output Current Source ($V_{CC} = 15\text{ V}$, $V_{OUT} = 2\text{ V}$, $V_{ID} = +1\text{ V}$)		20	40		mA
I_O	Short-Circuit to GND ($V_{CC} = 15\text{ V}$)			40	60	mA
I_{SINK}	Output Current Sink ($V_{ID} = -1\text{ V}$)	$V_{CC} = +15\text{ V}$, $V_{OUT} = 0.2\text{ V}$	1	10		mA
		$V_{CC} = +15\text{ V}$, $V_{OUT} = 2\text{ V}$	10	20		mA
V_{OH}	Output Voltage Swing, High ($V_{CC} = 30\text{ V}$)	$R_L = 2\text{ k}\Omega$, $T_A = 25^\circ\text{C}$	26	27		V
		$-40 \leq T_A \leq +105^\circ\text{C}$	26			
		$R_L = 10\text{ k}\Omega$, $T_A = 25^\circ\text{C}$	27	28		
		$-40 \leq T_A \leq +105^\circ\text{C}$	27			
V_{OL}	Output Voltage Swing, Low	$R_L = 10\text{ k}\Omega$, $T_A = 25^\circ\text{C}$		5.0	50	mV
		$-40 \leq T_A \leq +105^\circ\text{C}$			50	
SR	Slew Rate ($A_V = +1$, $V_i = 0.5\text{ V}$ to 3 V , $V_{CC} = 15\text{ V}$, $R_L = 2\text{ k}\Omega$, $C_L = 100\text{ pF}$)		0.2	0.4		V/ μs
GBP	Gain Bandwidth Product ($V_{CC} = 30\text{ V}$, $A_V = +1$, $R_L = 2\text{ k}\Omega$, $C_L = 100\text{ pF}$, $f = 100\text{ kHz}$, $V_{IN} = 10\text{ mV}_{PP}$) (Note 4)		0.5	0.9		MHz
THD	Total Harmonic Distortion ($f = 1\text{ kHz}$, $A_V = 10$, $R_L = 2\text{ k}\Omega$, $V_{CC} = 30\text{ V}$, $V_{OUT} = 2\text{ V}_{PP}$)			0.08		%
e_{noise}	Equivalent Input Noise Voltage ($f = 1\text{ kHz}$, $R_S = 100\ \Omega$, $V_{CC} = 30\text{ V}$)			50		nV/ $\sqrt{\text{Hz}}$

VOLTAGE REFERENCE

I_K	Cathode Current		0.075		100	mA
V_{ref}	Reference Voltage ($I_K = 1\text{ mA}$)	$T_A = 25^\circ\text{C}$	2.49	2.5	2.51	V
		$-40 \leq T_A \leq +105^\circ\text{C}$	2.48	2.5	2.52	
ΔV_{ref}	Reference Deviation over Temperature ($V_{KA} = V_{ref}$, $I_K = 10\text{ mA}$, $-40 \leq T_A \leq +105^\circ\text{C}$) (Note 4)			7.0	30	mV
I_{min}	Minimum Cathode Current for Regulation ($V_{KA} \geq 2.45\text{ V}_I$)			40	75	μA
$ Z_{KA} $	Dynamic Impedance (Note 3) ($V_{KA} = V_{ref}$, $I_K = 1\text{ mA}$ to 100 mA , $f < 1\text{ kHz}$)			0.2	0.5	Ω

- The input common-mode voltage of either input signal should not be allowed to go negative by more than 0.3 V. The upper end of the common-mode range is $V_{CC} - 1.5\text{ V}$. Both inputs can go to $V_{CC} + 0.3\text{ V}$ without damage.
- The Dynamic Impedance is defined as $|Z_{KA}| = \Delta V_{KA} / \Delta I_K$.
- Guaranteed by design and/or characterization.

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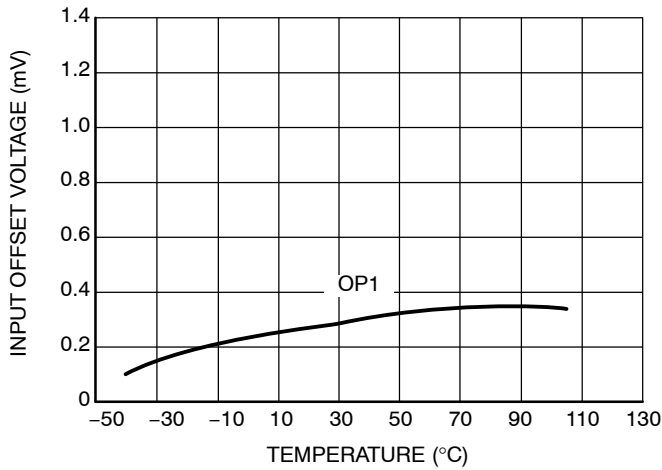


Figure 1. Input Offset Voltage vs. Temperature

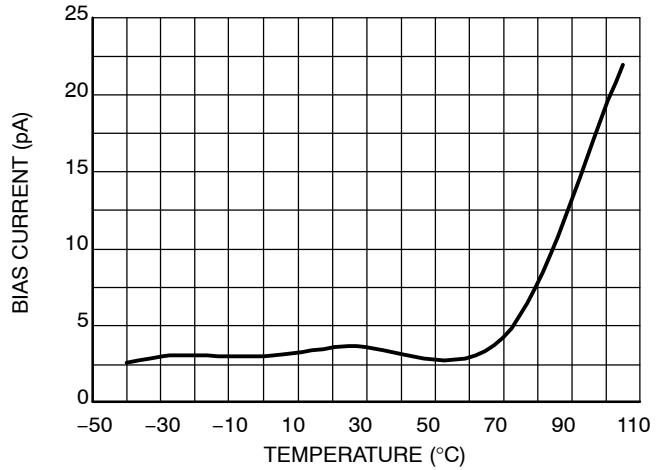


Figure 2. IB vs. Temperature

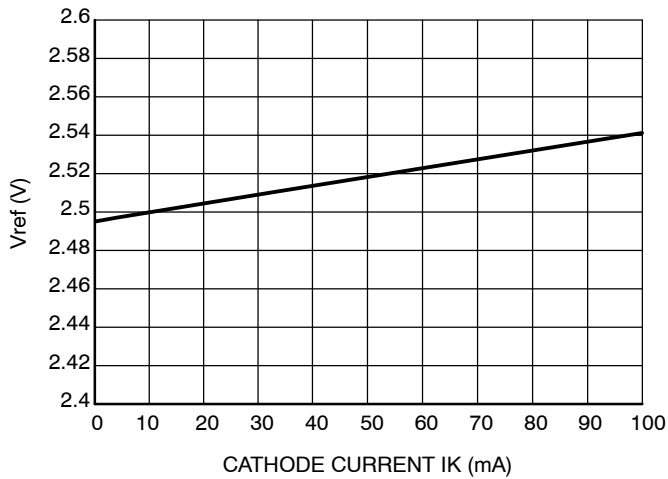


Figure 3. Vref as a Function of IK

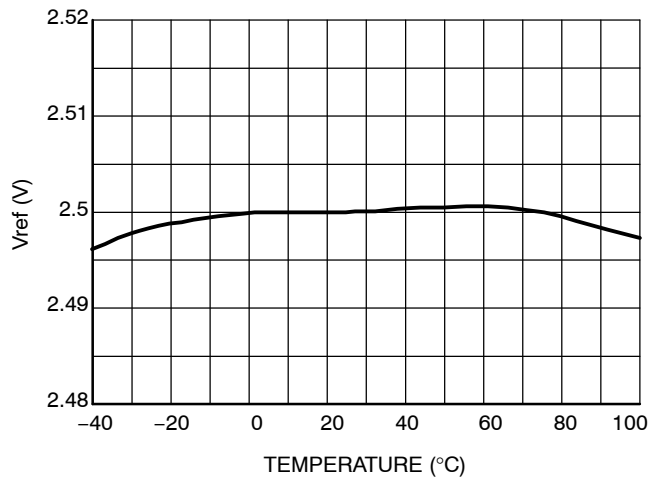


Figure 4. Vref Over Temperature

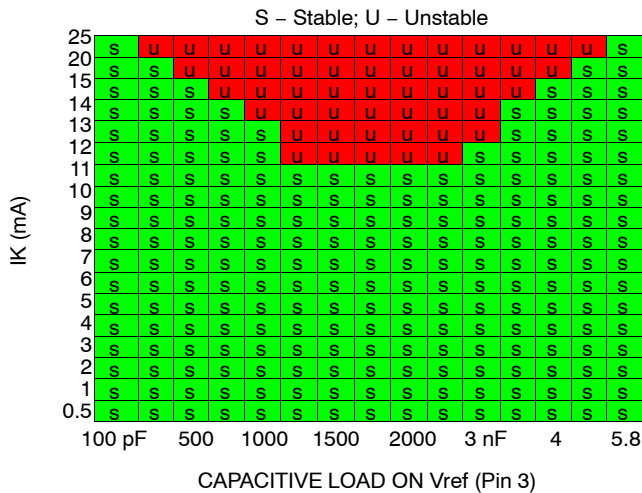


Figure 5. Region of Reference Stability vs. Capacitive Load (Pin 3)

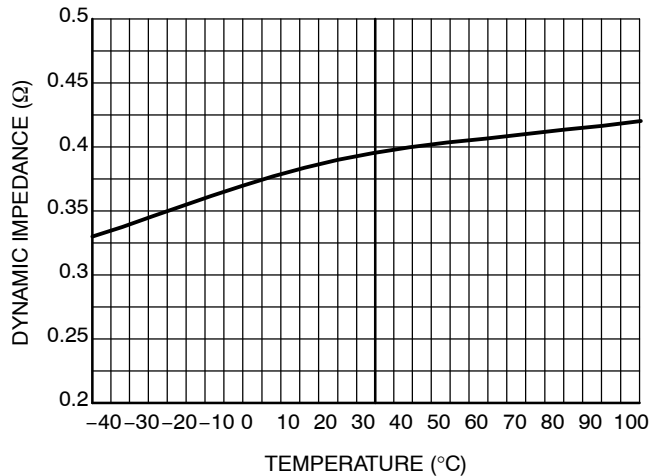


Figure 6. Ref Dynamic Impedance vs. Temperature

NCS1002

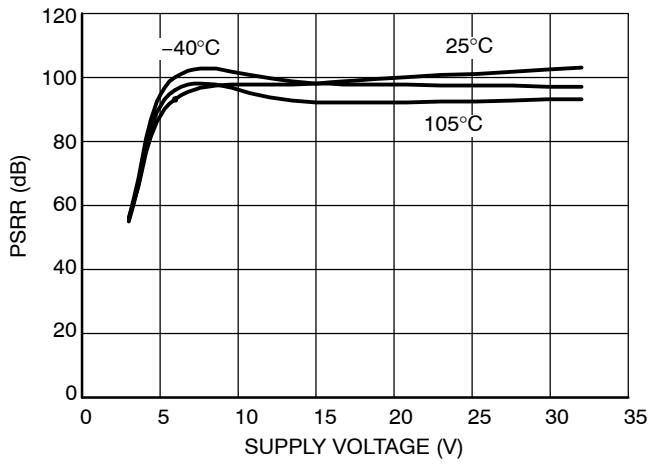


Figure 7. NCS1002 PSRR vs. Supply Voltage

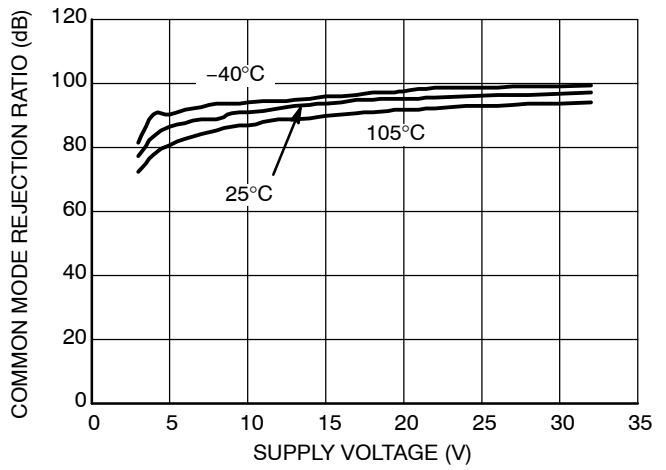


Figure 8. NCS1002 CMRR vs. Supply Voltage

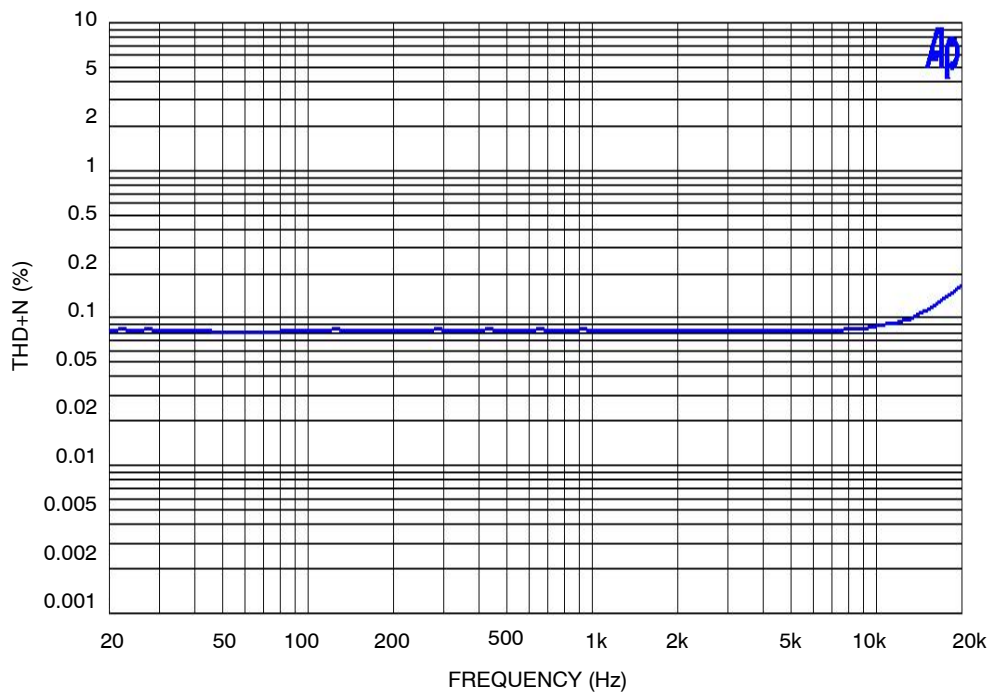


Figure 9. THD+N

NCS1002

ORDERING INFORMATION

Device	Package	Shipping†
NCS1002DR2G	SOIC-8 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 1:1

SOIC-8 NB
CASE 751-07
ISSUE AK

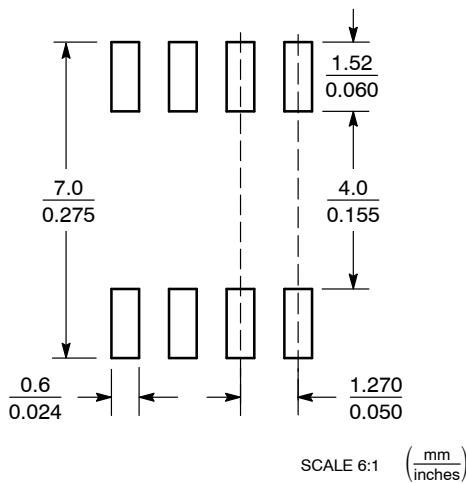
DATE 16 FEB 2011



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
 6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.80	5.00	0.189	0.197
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27 BSC		0.050 BSC	
H	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
M	0°	8°	0°	8°
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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DESCRIPTION:	SOIC-8 NB	PAGE 1 OF 2

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SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011

- | | | | |
|--|---|---|---|
| <p>STYLE 1:
 PIN 1. EMITTER
 2. COLLECTOR
 3. COLLECTOR
 4. EMITTER
 5. EMITTER
 6. BASE
 7. BASE
 8. EMITTER</p> | <p>STYLE 2:
 PIN 1. COLLECTOR, DIE, #1
 2. COLLECTOR, #1
 3. COLLECTOR, #2
 4. COLLECTOR, #2
 5. BASE, #2
 6. EMITTER, #2
 7. BASE, #1
 8. EMITTER, #1</p> | <p>STYLE 3:
 PIN 1. DRAIN, DIE #1
 2. DRAIN, #1
 3. DRAIN, #2
 4. DRAIN, #2
 5. GATE, #2
 6. SOURCE, #2
 7. GATE, #1
 8. SOURCE, #1</p> | <p>STYLE 4:
 PIN 1. ANODE
 2. ANODE
 3. ANODE
 4. ANODE
 5. ANODE
 6. ANODE
 7. ANODE
 8. COMMON CATHODE</p> |
| <p>STYLE 5:
 PIN 1. DRAIN
 2. DRAIN
 3. DRAIN
 4. DRAIN
 5. GATE
 6. GATE
 7. SOURCE
 8. SOURCE</p> | <p>STYLE 6:
 PIN 1. SOURCE
 2. DRAIN
 3. DRAIN
 4. SOURCE
 5. SOURCE
 6. GATE
 7. GATE
 8. SOURCE</p> | <p>STYLE 7:
 PIN 1. INPUT
 2. EXTERNAL BYPASS
 3. THIRD STAGE SOURCE
 4. GROUND
 5. DRAIN
 6. GATE 3
 7. SECOND STAGE Vd
 8. FIRST STAGE Vd</p> | <p>STYLE 8:
 PIN 1. COLLECTOR, DIE #1
 2. BASE, #1
 3. BASE, #2
 4. COLLECTOR, #2
 5. COLLECTOR, #2
 6. EMITTER, #2
 7. EMITTER, #1
 8. COLLECTOR, #1</p> |
| <p>STYLE 9:
 PIN 1. EMITTER, COMMON
 2. COLLECTOR, DIE #1
 3. COLLECTOR, DIE #2
 4. EMITTER, COMMON
 5. EMITTER, COMMON
 6. BASE, DIE #2
 7. BASE, DIE #1
 8. EMITTER, COMMON</p> | <p>STYLE 10:
 PIN 1. GROUND
 2. BIAS 1
 3. OUTPUT
 4. GROUND
 5. GROUND
 6. BIAS 2
 7. INPUT
 8. GROUND</p> | <p>STYLE 11:
 PIN 1. SOURCE 1
 2. GATE 1
 3. SOURCE 2
 4. GATE 2
 5. DRAIN 2
 6. DRAIN 2
 7. DRAIN 1
 8. DRAIN 1</p> | <p>STYLE 12:
 PIN 1. SOURCE
 2. SOURCE
 3. SOURCE
 4. GATE
 5. DRAIN
 6. DRAIN
 7. DRAIN
 8. DRAIN</p> |
| <p>STYLE 13:
 PIN 1. N.C.
 2. SOURCE
 3. SOURCE
 4. GATE
 5. DRAIN
 6. DRAIN
 7. DRAIN
 8. DRAIN</p> | <p>STYLE 14:
 PIN 1. N-SOURCE
 2. N-GATE
 3. P-SOURCE
 4. P-GATE
 5. P-DRAIN
 6. P-DRAIN
 7. N-DRAIN
 8. N-DRAIN</p> | <p>STYLE 15:
 PIN 1. ANODE 1
 2. ANODE 1
 3. ANODE 1
 4. ANODE 1
 5. CATHODE, COMMON
 6. CATHODE, COMMON
 7. CATHODE, COMMON
 8. CATHODE, COMMON</p> | <p>STYLE 16:
 PIN 1. EMITTER, DIE #1
 2. BASE, DIE #1
 3. EMITTER, DIE #2
 4. BASE, DIE #2
 5. COLLECTOR, DIE #2
 6. COLLECTOR, DIE #2
 7. COLLECTOR, DIE #1
 8. COLLECTOR, DIE #1</p> |
| <p>STYLE 17:
 PIN 1. VCC
 2. V2OUT
 3. V1OUT
 4. TXE
 5. RXE
 6. VEE
 7. GND
 8. ACC</p> | <p>STYLE 18:
 PIN 1. ANODE
 2. ANODE
 3. SOURCE
 4. GATE
 5. DRAIN
 6. DRAIN
 7. CATHODE
 8. CATHODE</p> | <p>STYLE 19:
 PIN 1. SOURCE 1
 2. GATE 1
 3. SOURCE 2
 4. GATE 2
 5. DRAIN 2
 6. MIRROR 2
 7. DRAIN 1
 8. MIRROR 1</p> | <p>STYLE 20:
 PIN 1. SOURCE (N)
 2. GATE (N)
 3. SOURCE (P)
 4. GATE (P)
 5. DRAIN
 6. DRAIN
 7. DRAIN
 8. DRAIN</p> |
| <p>STYLE 21:
 PIN 1. CATHODE 1
 2. CATHODE 2
 3. CATHODE 3
 4. CATHODE 4
 5. CATHODE 5
 6. COMMON ANODE
 7. COMMON ANODE
 8. CATHODE 6</p> | <p>STYLE 22:
 PIN 1. I/O LINE 1
 2. COMMON CATHODE/VCC
 3. COMMON CATHODE/VCC
 4. I/O LINE 3
 5. COMMON ANODE/GND
 6. I/O LINE 4
 7. I/O LINE 5
 8. COMMON ANODE/GND</p> | <p>STYLE 23:
 PIN 1. LINE 1 IN
 2. COMMON ANODE/GND
 3. COMMON ANODE/GND
 4. LINE 2 IN
 5. LINE 2 OUT
 6. COMMON ANODE/GND
 7. COMMON ANODE/GND
 8. LINE 1 OUT</p> | <p>STYLE 24:
 PIN 1. BASE
 2. EMITTER
 3. COLLECTOR/ANODE
 4. COLLECTOR/ANODE
 5. CATHODE
 6. CATHODE
 7. COLLECTOR/ANODE
 8. COLLECTOR/ANODE</p> |
| <p>STYLE 25:
 PIN 1. VIN
 2. N/C
 3. REXT
 4. GND
 5. IOUT
 6. IOUT
 7. IOUT
 8. IOUT</p> | <p>STYLE 26:
 PIN 1. GND
 2. dv/dt
 3. ENABLE
 4. ILIMIT
 5. SOURCE
 6. SOURCE
 7. SOURCE
 8. VCC</p> | <p>STYLE 27:
 PIN 1. ILIMIT
 2. OVLO
 3. UVLO
 4. INPUT+
 5. SOURCE
 6. SOURCE
 7. SOURCE
 8. DRAIN</p> | <p>STYLE 28:
 PIN 1. SW_TO_GND
 2. DASIC OFF
 3. DASIC_SW_DET
 4. GND
 5. V_MON
 6. VBULK
 7. VBULK
 8. VIN</p> |
| <p>STYLE 29:
 PIN 1. BASE, DIE #1
 2. EMITTER, #1
 3. BASE, #2
 4. EMITTER, #2
 5. COLLECTOR, #2
 6. COLLECTOR, #2
 7. COLLECTOR, #1
 8. COLLECTOR, #1</p> | <p>STYLE 30:
 PIN 1. DRAIN 1
 2. DRAIN 1
 3. GATE 2
 4. SOURCE 2
 5. SOURCE 1/DRAIN 2
 6. SOURCE 1/DRAIN 2
 7. SOURCE 1/DRAIN 2
 8. GATE 1</p> | | |

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